

IN THE CLAIMS (as amended During International Preliminary Examination):

Please amend the claims as follows:

1. (Currently Amended) A method for ~~the production of producing~~ a spherical or grain-shaped semiconductor element (11) for use in a solar cell, characterized by comprising the following steps of:

— application of applying a conductive back contact layer (30) onto a spherical or grain-shaped substrate core (20);

— application of applying a first precursor layer (40) ~~made of~~ comprising copper or copper gallium;

— application of applying a second precursor layer (50) ~~made of~~ comprising indium; and

— reaction of reacting the precursor layers (40) and (50) with sulfur and/or selenium to form a I-III-VI compound semiconductor, whereby the by carrying out the reaction of the layer structure (10) ~~is carried out~~ in a melt of the reaction element sulfur or selenium, or carrying out the reaction of the layer structure (10) ~~is carried out~~ in hydrogen compounds of the reaction element sulfur or selenium, whereby carrying out the reaction in hydrogen compounds ~~is carried out at or below atmospheric pressure or at a pressure lower than atmospheric pressure.~~

2. (Currently Amended) The method according to claim 1, characterized in that wherein the main constituent of the conductive back contact layer (30) is molybdenum.

3. (Currently Amended) The method according to claim 2, characterized in that wherein the conductive back contact layer (30) contains up to 20% by weight of gallium in order to improve the adhesion.

4. (Currently Amended) The method according to ~~one or more of the preceding claims~~ claim 1, characterized in that comprising applying each of the layers (30; 40; 50) are each applied by means of a PVD or CVD methods method.

5. (Currently Amended) The method according to ~~one or more of the preceding claims~~ claim 1, characterized in that comprising alloys on a layer structure (10) comprising precursor layers (40; 50) is ~~alloyed~~ at a temperature of $T > 220^{\circ}\text{C}$ [$> 428^{\circ}\text{F}$] prior to the reaction to form a I-III-VI compound semiconductor.

6. (Currently Amended) The method according to ~~one or more of the preceding claims~~ claim 1, characterized in that comprising carrying out a treatment with a KCN solution ~~is carried out after the reaction of reacting~~ the layer structure (10) to form a I-III-VI compound semiconductor.

7. (Currently Amended) The method according to ~~one or more of the preceding claims~~ claim 1, characterized in that comprising depositing a buffer layer ~~is deposited after the reaction of reacting~~ the layer structure (10) to form a I-III-VI compound semiconductor.

8. (Currently Amended) The method according to ~~one or more of the preceding claims~~ claim 1, characterized in that comprising depositing a high-resistance ZnO layer and a low-resistance ZnO layer ~~are deposited after the reaction of reacting~~ the layer structure (10) to form a I-III-VI compound semiconductor.

9. (Currently Amended) The method according to ~~one or both of the preceding claims~~ ~~claim 7 and 8, characterized in that~~ comprising depositing the buffer layer and/or the high-resistance and the low-resistance layers are deposited by means of a PVD or CVD methods method.

10. (Currently Amended) A spherical or grain-shaped semiconductor element for use in solar cells, ~~characterized in that~~ wherein the semiconductor element (11) has a spherical or grain-shaped substrate core (20) that ~~consists of~~ comprising soda-lime glass and that is coated at least with one back contact layer (30) ~~made of~~ comprising molybdenum and with one I-III-VI compound semiconductor.

11. (Currently Amended) The semiconductor element according to claim 10, ~~characterized in that~~ wherein the diameter of the substrate core (20) is in the order of magnitude of 0.1 mm to 1 mm, ~~especially approximately 0.2 mm~~.

12. (Currently Amended) The semiconductor element according to ~~one or more of claims~~ ~~claim 10 and 11, characterized in that~~ wherein the thickness of the back contact layer (30) is in the order of magnitude of 0.1 μm to 1 μm .

13. (Currently Amended) The semiconductor element according to ~~one or more of claims~~ ~~claim 10 to 12, characterized in that~~ wherein the I-III-VI compound semiconductor layer (60) ~~consists of~~ comprising a compound from selected from the group consisting of the copper indium sulfides, copper indium diselenides, copper indium gallium sulfides ~~or, and~~ copper indium gallium diselenides.

14. (Currently Amended) The semiconductor element according to ~~one or more of~~
~~claims claim 10 to 13, characterized in that wherein~~ the thickness of the I-III-VI compound
semiconductor layer (60) is in the order of magnitude of 1 μm to 3 μm .

15. (Currently Amended) The semiconductor element according to ~~one or more of~~
~~claims claim 10 to 14, characterized in that wherein~~ the semiconductor element (11) has a
buffer layer above the I-III-VI compound semiconductor layer (60).

16. (Currently Amended) The semiconductor element according to claim 15,
~~characterized in that wherein~~ the buffer layer ~~consists of~~ comprises a material selected from
the group ~~comprising~~ consisting of CdS, ZnS, ZnSe, ZnO, indium selenium compounds or
indium sulfur compounds.

17. (Currently Amended) The semiconductor element according to ~~one or both of~~
~~claims claim 15 and 16, characterized in that wherein~~ the thickness of the buffer layer is in
the order of magnitude of 20 nm to 200 nm.

18. (Currently Amended) The semiconductor element according to ~~one or more of~~
~~claims claim 10 to 17, characterized in that wherein~~ the semiconductor element has a high-
resistance and a low-resistance ZnO layer above the I-III-VI compound semiconductor layer
(60).

19. (Currently Amended) The semiconductor element according to claim 18,
~~characterized in that wherein~~ the thickness of the high-resistance layer is in the order of

magnitude of 10 nm to 100 nm, ~~whereas and which~~ the thickness of the low-resistance ZnO layer is in the order of magnitude of 0.1 μm to 2 μm .

20. (Currently Amended) The semiconductor element according to ~~one or more of claims claim 10 to 19, characterized in that wherein~~ the semiconductor element (11) was is produced by a method according to ~~one or more of claims~~ claim 1 to 9.

21. (Currently Amended) A method for ~~the production of producing~~ a solar cell having integrated spherical or grain-shaped semiconductor elements, ~~characterized by comprising the following features steps of:~~

— incorporation of incorporating several spherical or grain-shaped semiconductor elements (11) into an insulating support layer (70), ~~whereby, wherein~~ the semiconductor elements (11) protrude from the surface of the support layer on at least one side of the support layer, and the semiconductor elements (11) each consist of comprise a spherical or grain-shaped substrate core (20) that is coated at least with one conductive back contact layer (30) and with one I-III-VI compound semiconductor layer (60);

— removal of removing parts of the semiconductor elements (11) on one side of the support layer (70) so that a surface of the conductive back contact layer (30) of the semiconductor elements (11) is exposed;

— application of applying a back contact layer (80) onto the a side of the support layer (70) on which parts of the semiconductor elements (11) have been removed; and

— application of applying a front contact layer (90) onto the side of the support layer (70) on which no semiconductor elements (11) have been removed.

22. (Currently Amended) The method according to claim 21, characterized in that comprising, in addition to parts of the semiconductor elements (11), removing part of the support layer (70) is also removed.

23. (Currently Amended) The method according to one or both of claims claim 21 and 22, characterized in that comprising applying the semiconductor elements (11) are applied onto the support layer (70) by means of scattering, dusting and/or printing and they are subsequently incorporated the semiconductor elements into the support layer.

24. (Currently Amended) The method according to one or more of claims claim 21 to 23, characterized in that comprising configuring the support layer (70) is configured as a matrix with recesses into which the semiconductor elements (11) are incorporated.

25. (Currently Amended) The method according to one or more of claims claim 21 to 24, characterized in that comprising incorporating the semiconductor elements (11) are incorporated into the support layer (70) by means of a heating and/or pressing procedure.

26. (Currently Amended) The method according to one or more of claims claim 21 to 25, characterized in that the removal of comprising removing the semiconductor elements (11) and/or of the support layer (70) is done by grinding, polishing, etching, thermal energy input and/or by or a photolithographic processes process.

27. (Currently Amended) The method according to one or more of claims claim 21 to 26, characterized in that comprising depositing the back contact layer (80) and/or the

front contact layer (90) are deposited by a PVD or CVD methods method or by methods another method adapted to the material of the layer in question.

28. (Currently Amended) A solar cell having integrated spherical or grain-shaped semiconductor elements, characterized in that the solar cell has at least the following features comprising:

[[•]] an insulating support layer (70) into which the spherical or grain-shaped semiconductor elements (11) are incorporated, whereby wherein the semiconductor elements (11) protrude from the layer on at least one side of the support layer (70), and the semiconductor elements (11) each consist of comprising a spherical or grain-shaped substrate core (20) that is coated at least with one conductive back contact layer (30) and with one I-III-VI compound semiconductor layer;

[[•]] a back contact layer (80) on one side of the support layer (70), whereby several, wherein a plurality of semiconductor elements (11) on this side of the support layer have a surface that is free of I-III-VI compound semiconductors; and

[[•]] a front contact layer (90) on the side of the support layer (70) on which the semiconductor elements (11) do not have a surface that is free of I-III-VI compound semiconductors.

29. (Currently Amended) The solar cell according to claim 28, characterized in that it is produced by means of a method according to one or more of claims 21 to 27 comprising the steps of:

incorporating several spherical or grain-shaped semiconductor elements into an insulating support layer, wherein the semiconductor elements protrude from the surface of the support layer on at least one side of the support layer, and the semiconductor elements each

comprise a spherical or grain-shaped substrate core that is coated at least with one conductive back contact layer and with one I-III-VI compound semiconductor layer;

removing parts of the semiconductor elements on one side of the support layer so that a surface of the conductive back contact layer of the semiconductor elements is exposed;
applying a back contact layer onto a side of the support layer on which parts of the semiconductor elements have been removed; and

applying a front contact layer onto the side of the support layer on which no semiconductor elements have been removed.

30. (Currently Amended) The solar cell according to ~~one or both of claims~~ claim 28 and 29, characterized in that wherein the insulating support layer (70) ~~consists of~~ comprises a thermoplastic material.

31. (Currently Amended) The solar cell according to ~~one or more of the preceding~~ claims 28 to 30, characterized in that wherein the support layer (10) ~~consists of~~ comprises a polymer selected from the group consisting of the epoxides, polycarbonates, polyesters, polyurethanes, polyacrylics and/or, and polyimides.

32. (Currently Amended) The solar cell according to ~~one or more of the preceding~~ claims 28 to 31, characterized in that wherein the spherical or grain-shaped semiconductor elements (11) are semiconductor elements according to ~~one or more of claims~~ 10 to 20, wherein the semiconductor element has a spherical or grain-shaped substrate core comprising soda-lime glass and coated at least with one back contact layer comprising molybdenum and one I-III-VI compound semiconductor.

33. (Currently Amended) The solar cell according to ~~one or more of claims~~ claim 28 to 32, characterized in that wherein the semiconductor elements (11) are coated with a I-III-VI compound semiconductor selected from the group consisting of the copper indium diselenides, copper indium disulfides, copper indium gallium diselenides and copper indium gallium diselenide disulfides.

34. (Currently Amended) The solar cell according to ~~one or more of claims~~ claim 28 to 33, characterized in that wherein the front contact layer (90) consists of comprises a conductive material.

35. (Currently Amended) The solar cell according to claim 34, characterized in that wherein the front contact layer (90) consists of comprises a transparent conductive oxide (TCO).

36. (Currently Amended) The solar cell according to ~~one or more of claims~~ claim 28 to 35, characterized in that wherein the back contact layer (80) consists of comprises a conductive material.

37. (Currently Amended) The solar cell according to claim 36, characterized in that wherein the back contact layer (80) consists of comprises a metal, a transparent conductive oxide (TCO) or a polymer having conductive particles.

38. (Currently Amended) The solar cell according to claim 37, characterized in that wherein the back contact layer (80) consists of comprises a polymer selected from the group consisting of the epoxy resins, polyurethanes and/or polyimides having conductive

particles selected from a the group comprising consisting of carbon, indium, nickel, molybdenum, iron, nickel chromium, silver, aluminum ~~and/or the~~ and corresponding alloys or oxides.

39. (Currently Amended) The solar cell according to claim 38, characterized in that wherein the back contact layer (80) consists of comprises an intrinsic conductive polymer.

40. (Currently Amended) A photovoltaic module, ~~characterized in that it has~~ comprising at least one solar cell according to ~~one or more of claims~~ claim 28 to 39.

41. (New) The semiconductor element according to claim 10, wherein the diameter of the substrate core is in the order of magnitude approximately 0.2 mm.